

800V 0.11Ω Super Junction Power MOSFET

Description

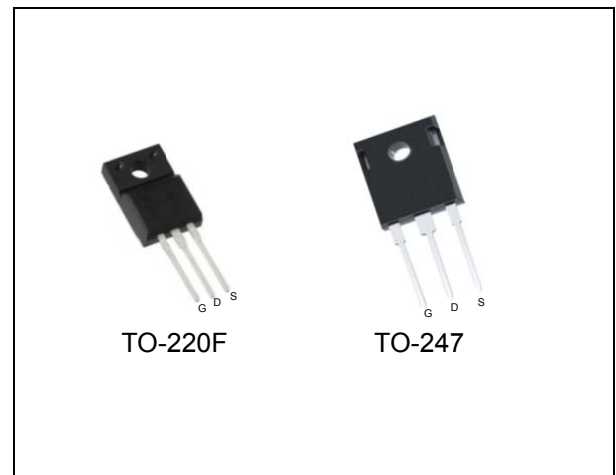
WMOS™ M3 is Wayon's 3rd generation 800V super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS™ M3 is suitable for applications which require superior power density and outstanding efficiency.

Features

- $V_{DS} = 850V @ T_{j,max}$
- Typ. $R_{DS(on)} = 0.11\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server



Absolute Maximum Ratings

Parameter	Symbol	WMJ	WML	Unit
Drain-source voltage	V_{DSS}	800		V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$)	I_D	32		A
		20		A
Pulsed drain current ²⁾	I_{DM}	115		A
Gate-source voltage	V_{GS}	± 30		V
Avalanche energy, single pulse ³⁾	E_{AS}	850		mJ
Avalanche energy, repetitive ²⁾	E_{AR}	1.2		mJ
Avalanche current, repetitive ²⁾	I_{AR}	5.5		A
Power dissipation ($T_C = 25^\circ C$) - Derate above $25^\circ C$	P_D	320	34	W
		2.56	0.27	W/ $^\circ C$
Operating and storage temperature range	T_{j}, T_{stg}	-55 to +150		$^\circ C$
Continuous diode forward current	I_S	32		A
Diode pulse current	$I_{S,pulse}$	115		A

Thermal Characteristics

Parameter	Symbol	WMJ	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.33	3.6	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	800	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25\text{mA}$	2	3	4	V
Drain cut-off current	I_{DSS}	$V_{DS}=800\text{ V}, V_{GS}=0\text{V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	10	μA
Gate leakage current, forward	I_{GSSF}	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	nA
Gate leakage current, reverse	I_{GSSR}	$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=10\text{A}$ $T_j = 25^\circ\text{C}$	-	0.11	0.128	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS}=100\text{V}, V_{GS}=0\text{V},$	-	4470	-	pF
Output capacitance	C_{oss}	$f = 1\text{ MHz}$	-	116	-	
Reverse transfer capacitance	C_{rss}		-	2.0	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 300\text{V}, I_D = 15\text{A}$	-	73	-	ns
Rise time	t_r	$R_G = 25\Omega, V_{GS}=10\text{V}$	-	81	-	
Turn-off delay time	$t_{d(off)}$		-	280	-	
Fall time	t_f		-	54	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=480\text{V}, I_D=15\text{A},$	-	21.5	-	nC
Gate to drain charge	Q_{gd}	$V_{GS}=0\text{ to }10\text{V}$	-	32	-	
Gate charge total	Q_g		-	88.5	-	
Gate plateau voltage	$V_{plateau}$		-	5.3	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=15\text{A}$	-	-	1.2	V
Reverse recovery time	t_{rr}	$V_R=50\text{V}, I_F=15\text{A},$	-	320	-	ns
Reverse recovery charge	Q_{rr}	$di_f/dt=100\text{A}/\mu\text{s}$	-	5.5	-	μC
Peak reverse recovery current	I_{rrm}		-	29	-	A

Notes:

- Limited by $T_{j\max}$. Maximum duty cycle $D=0.5$.
- Repetitive rating: pulse width limited by maximum junction temperature.
- $I_{AS} = 5.5\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, starting $T_j = 25^\circ\text{C}$.

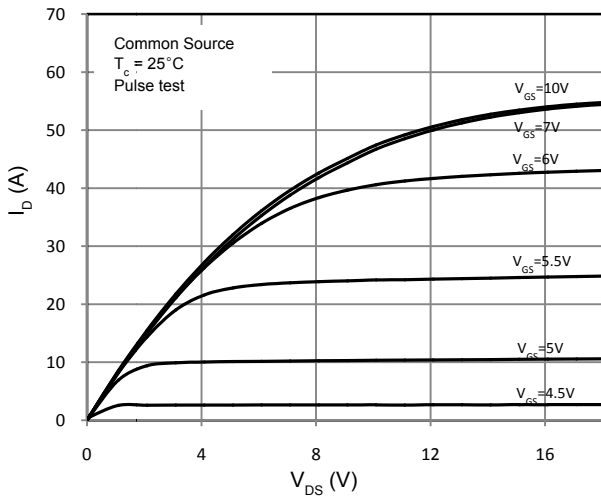


Figure 1. On-Region Characteristics

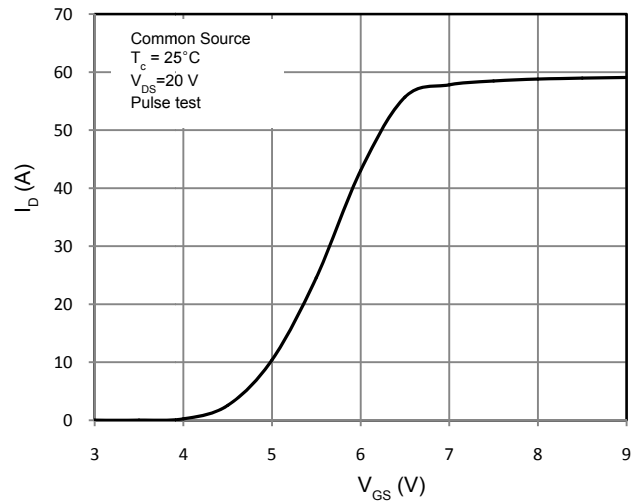


Figure 2. Transfer Characteristics

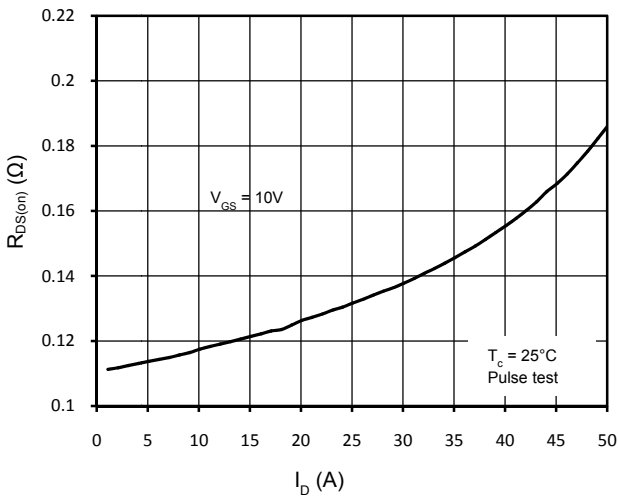


Figure 3. Static Drain-Source On Resistance

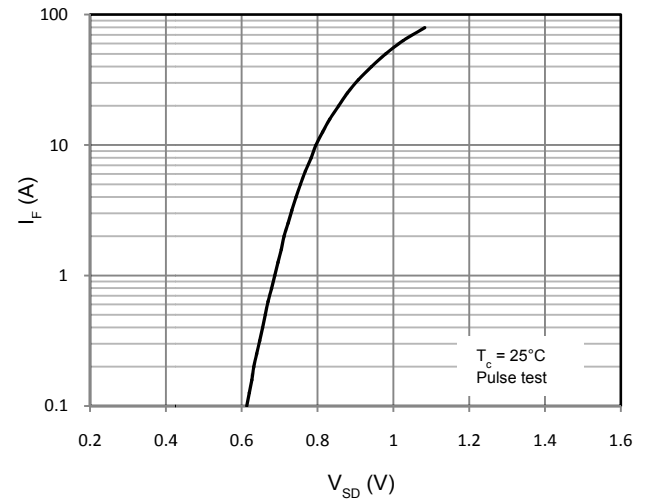


Figure 4. Body-Diode Forward Characteristics

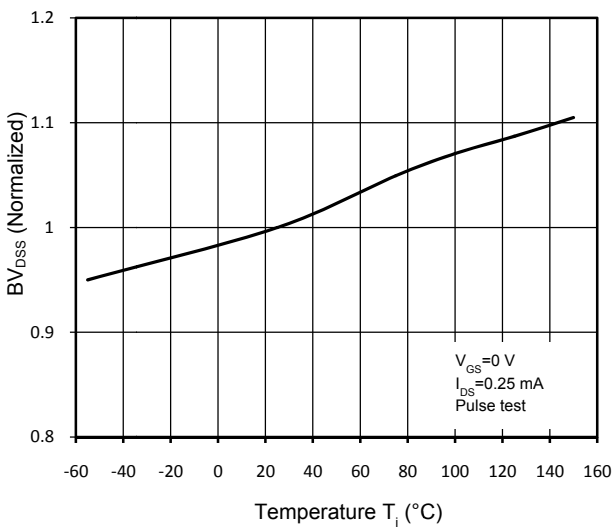


Figure 5. Normalized $BV_{DS(s)}$ vs. Temperature

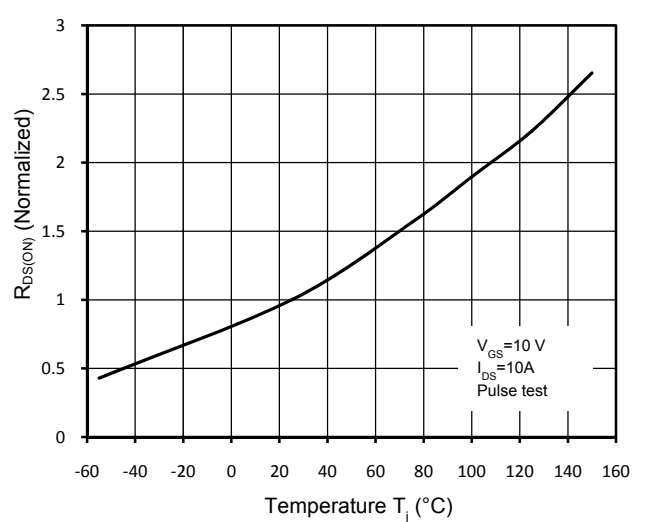


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

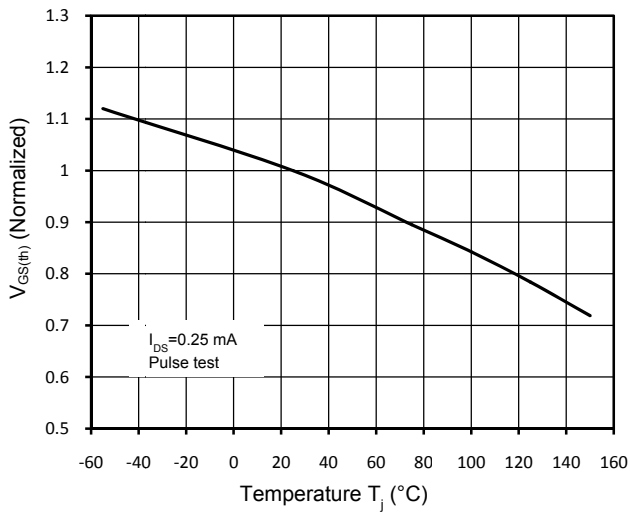


Figure 7. Threshold Voltage vs. Temperature

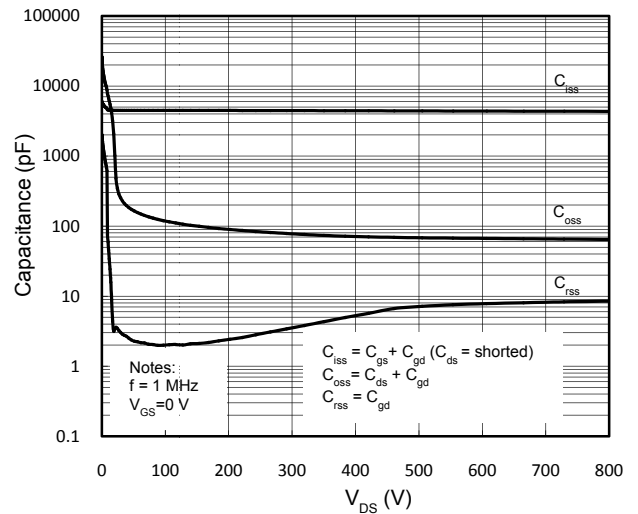


Figure 8. Capacitance Characteristics

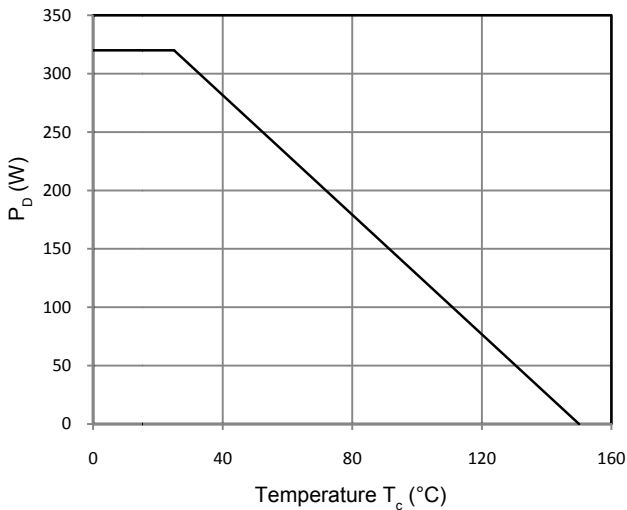


Figure 9. Power Dissipation

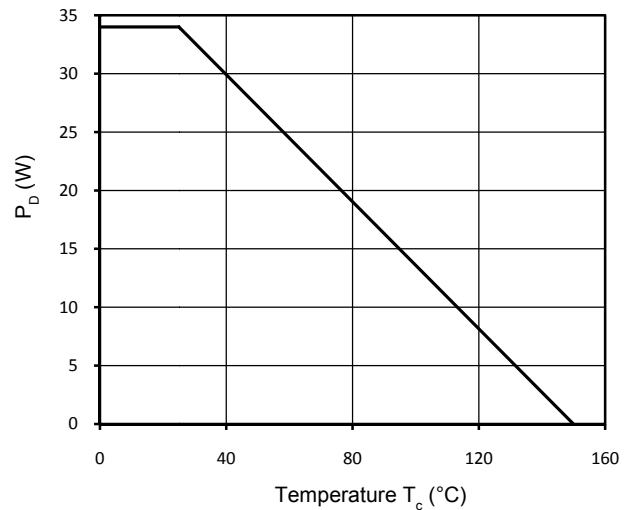


Figure 10. Power Dissipation (TO-220F)

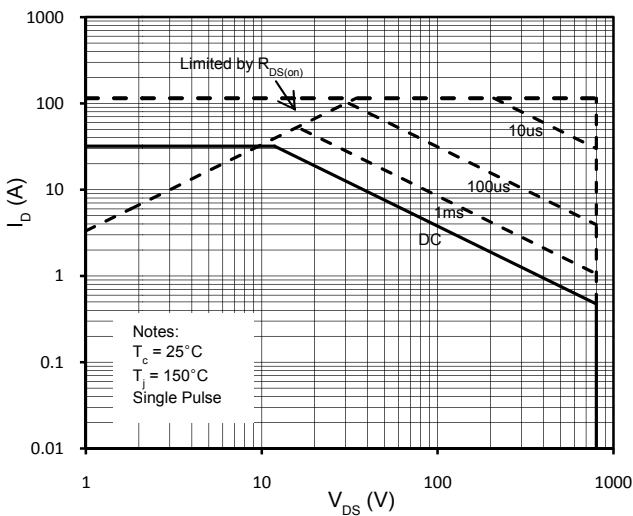


Figure 11. Maximum Safe Operating Area

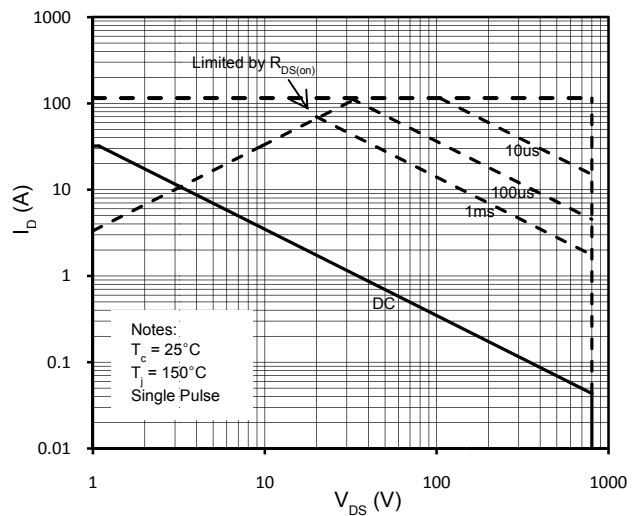


Figure 12. Maximum Safe Operating Area (TO-220F)

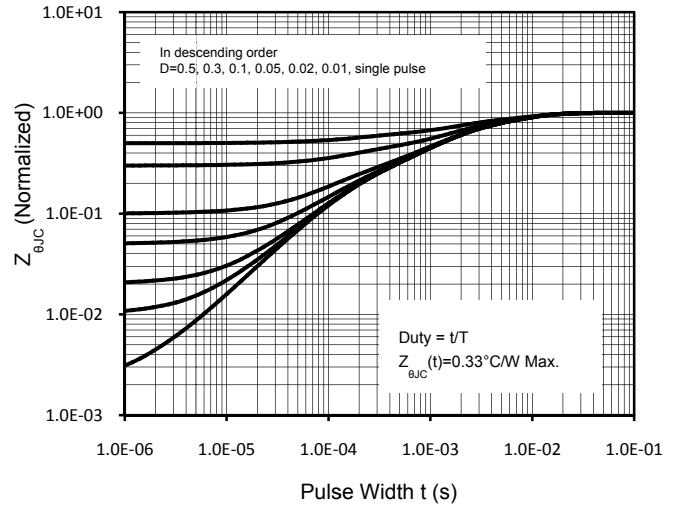
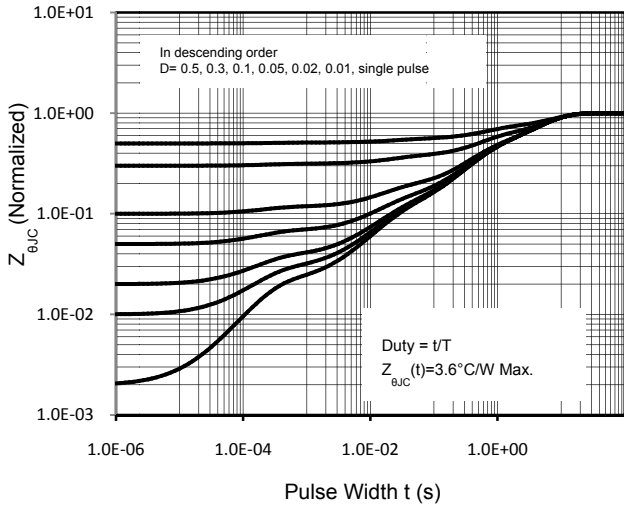


Figure 13. Transient Thermal Response Curve (TO-220F) Figure 14. Transient Thermal Response Curve

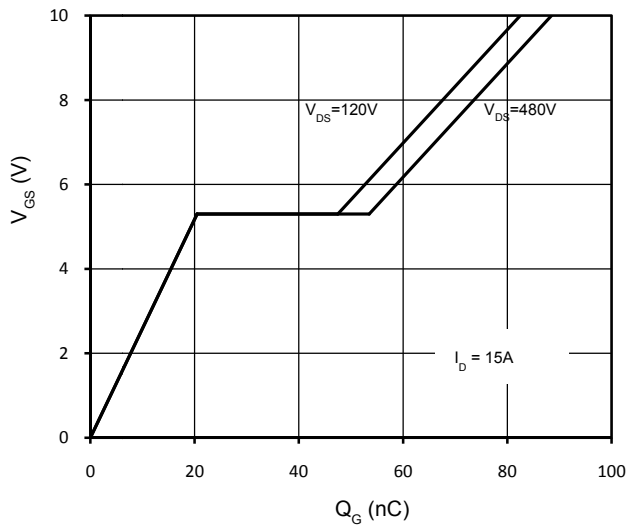


Figure 15. Gate Charge Characteristics

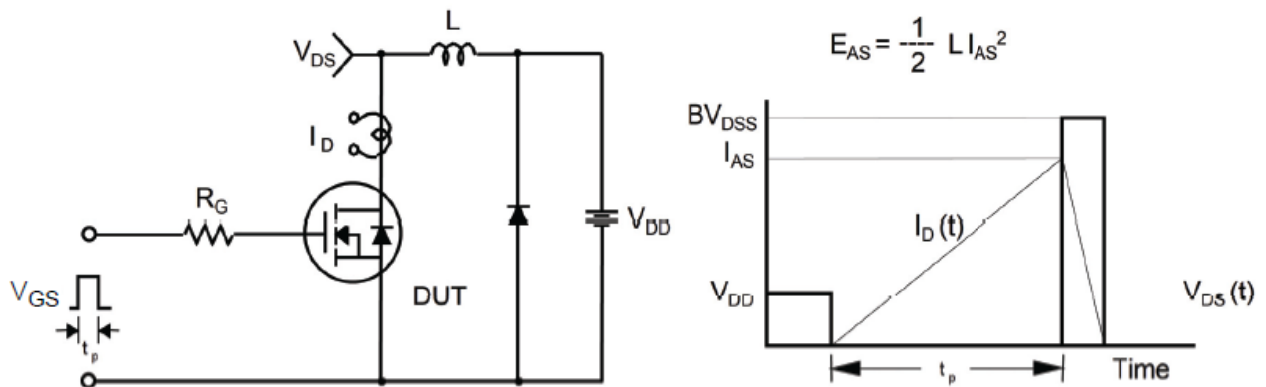
Gate Charge Test Circuit & Waveform



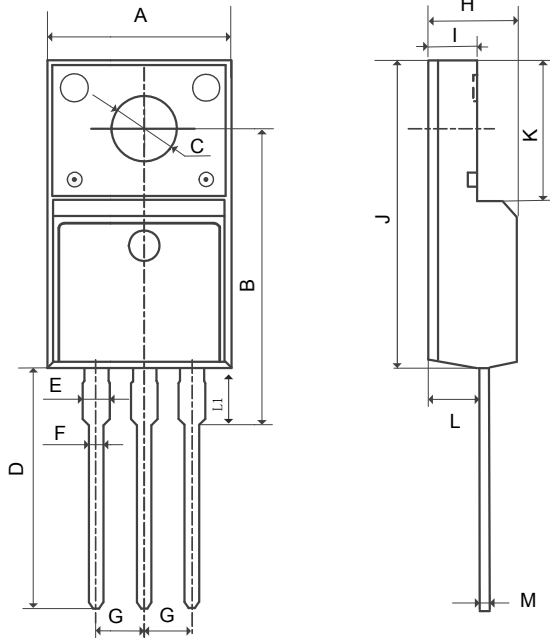
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for TO-220F

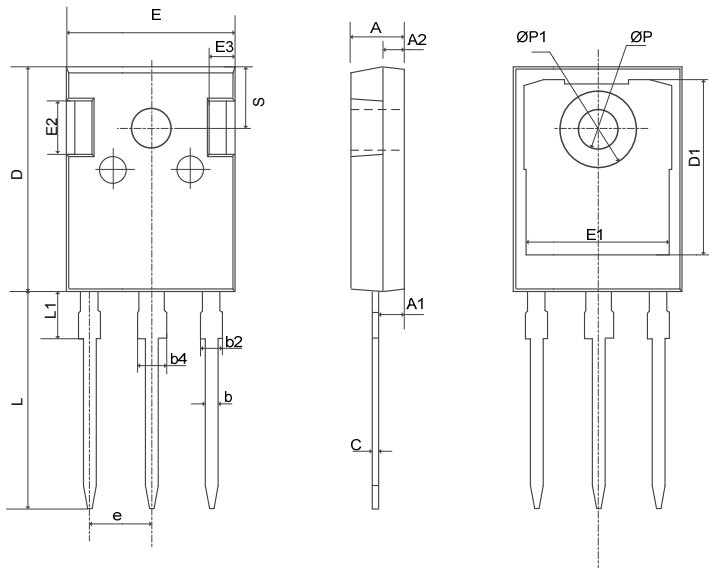


COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.20	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

Mechanical Dimensions for TO-247

COMMON DIMENSIONS

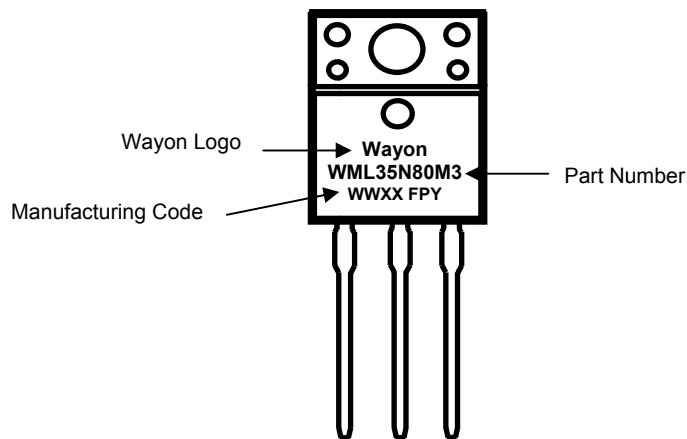


SYMBOL	MM	
	MIN	MAX
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.11	1.36
b2	1.91	2.21
b4	2.91	3.21
c	0.51	0.75
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.00	13.60
E2	4.80	5.20
E3	2.30	2.70
e	5.44BSC	
L	19.62	20.22
L1	—	4.30
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	

Ordering Information

Part	Package	Marking	Packing method
WML35N80M3	TO-220F	WML35N80M3	Tube
WMJ35N80M3	TO-247	WMJ35N80M3	Tube

Marking Information



Contact Information

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